DISCRETE SEMICONDUCTORS

DATA SHEET

PMBF4391; PMBF4392; PMBF4393

N-channel FETs

Product specification

April 1995



N-channel FETs

PMBF4391; PMBF4392; PMBF4393

DESCRIPTION

Symmetrical silicon n-channel depletion type junction field-effect transistors on a plastic microminiature envelope intended for application in thick and thin-film circuits. The transistors are intended for low-power chopper or switching applications in industry.

PINNING

1 = drain

2 = source

3 = gate

Note

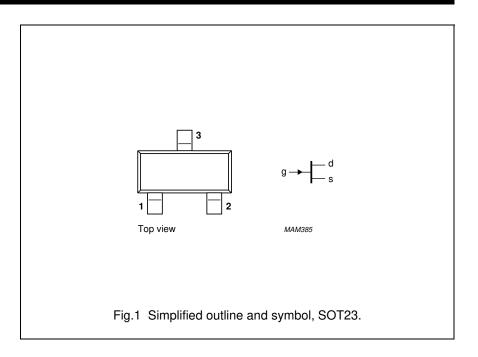
1. Drain and source are interchangeable.

Marking code

PMBF4391 = p6J

PMBF4392 = p6K

PMBF4393 = p6G



QUICK REFERENCE DATA

		PMBF4391		PMBF4392 PMBF4		F4393
Drain-source voltage	$\pm \ V_{DS}$	max.	40	40	40	V
Drain current						
$V_{DS} = 20 \text{ V}; V_{GS} = 0$	I_{DSS}	>	50	25	5	mA
Gate-source cut-off voltage						
V 20 V: 1 1 nA	V	>	4	2	0.5	V
$V_{DS} = 20 \text{ V}; I_D = 1 \text{ nA}$	$-V_{(P)GS}$	<	10	5	3	V
Drain-source resistance (on) at f = 1 kHz						
$I_D = 0; V_{GS} = 0$	$R_{ds \ on}$	<	30	60	100	Ω
Feedback capacitance at f = 1 MHz						
$-V_{GS} = 12 \text{ V}; V_{DS} = 0$	C_{rs}	<	3.5	3.5	3.5	pF
Turn-off time						
$V_{DD} = 10 \text{ V}; V_{GS} = 0$						
$I_D = 12 \text{ mA}; -V_{GSM} = 12 \text{ V}$	$t_{\rm off}$	<	20	_	_	ns
$I_D = 6 \text{ mA}; -V_{GSM} = 7 \text{ V}$	t_{off}	<	_	35	_	ns
$I_D = 3 \text{ mA}; -V_{GSM} = 5 \text{ V}$	t_{off}	<	-	_	50	ns

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RATINGS								
	accordance with the Absolute Max	kimum Svstem (IEC 13	34)				
Drain-source volta		, (√ _{DS}	max.	40	V	
Drain-gate voltage			± VDS V _{DGO}		max.	40		
Gate-source voltage				' _{GSO}	max.	40	V	
Gate current (DC)			I_{G}		max.		mA	
, ,	ation up to $T_{amb} = 40 ^{\circ}C^{(1)}$		P _{tot}		max.	250	mW	
Storage temperatu			Ts		-65 t	o + 150	°C	
Junction temperat	_	T _j		-9	max.	150	°C	
THERMAL RESIST	TANCE							
From junction to a	mbient ⁽¹⁾		Rt	h j-a	=	430	K/W	
CHARACTERISTIC								
$T_j = 25 ^{\circ}\text{C} \text{ unless o}$								
Gate-source voltage	•							
$I_G = 1 \text{ mA}; V_{DS} = 1 \text{ mA}$				V_{GSon}	<		1	V
Gate-source cut-o								
$V_{DS} = 0 \text{ V}; -V_{GS} = 20 \text{ V}$				-I _{GSS}	<		0.1	nA •
$V_{DS} = 0 \text{ V}; -V_{GS} = 20 \text{ V}; T_{amb} = 150 \text{ °C}$		-l _{GSS}	< 		0.2	μ A		
			РМЕ	3F4391	PMBF43	a 2	PMBF	74393
			1 1011		1 11151 10			
Drain current	0	I _{DSS}	>	50	1 11121 10	25	5	mA
Drain current V _{DS} = 20 V; V _{GS}	_S = 0	I_{DSS}	-		1 11151 10			
		I _{DSS}	>	50	121 10	25	5	mA
$V_{DS} = 20 \text{ V}; V_{GS}$	kdown voltage	I _{DSS} -V _{(BR)GSS}	>	50		25	5	mA
$V_{DS} = 20 \text{ V}; V_{GS}$ Gate-source break	kdown voltage = 0		> <	50 150		25 75	5 30	mA mA
V_{DS} = 20 V; V_{GS} Gate-source break $-I_G$ = 1 μ A; V_{DS}	kdown voltage = 0 ff voltage	−V _(BR) GSS	> <	50 150		25 75 40	5 30 40	mA mA
V_{DS} = 20 V; V_{GS} Gate-source break $-I_G$ = 1 μ A; V_{DS} Gate-source cut-o I_D = 1 nA; V_{DS} = Drain-source volta	xdown voltage = 0 ff voltage = 20 V age (on)	−V _(BR) GSS −V _(P) GS	> < < > >	50 150 40 4 10		25 75 40 2	5 30 40 0.5	mA mA
V_{DS} = 20 V; V_{GS} Gate-source break $-I_G$ = 1 μ A; V_{DS} Gate-source cut-o I_D = 1 nA; V_{DS} = Drain-source volta I_D = 12 mA; V_{GS}	cdown voltage = 0 ff voltage = 20 V age (on) $s = 0$	$-V_{(BR)GSS}$ $-V_{(P)GS}$ V_{DSon}	> < < > >	50 150 40 4		25 75 40 2 5	5 30 40 0.5	mA mA
V_{DS} = 20 V; V_{GS} Gate-source break $-I_G$ = 1 μ A; V_{DS} Gate-source cut-o I_D = 1 nA; V_{DS} = Drain-source volta I_D = 12 mA; V_{GS} I_D = 6 mA; V_{GS}	xdown voltage = 0 ff voltage = 20 V age (on) a = 0 = 0	$\begin{array}{c} -V_{(BR)GSS} \\ -V_{(P)GS} \end{array}$ $\begin{array}{c} V_{DSon} \\ V_{DSon} \end{array}$	> <	50 150 40 4 10		25 75 40 2	5 30 40 0.5	mA mA V V V
$V_{DS} = 20 \text{ V; } V_{GS}$ Gate-source break $-I_G = 1 \mu\text{A; } V_{DS}$ Gate-source cut-o $I_D = 1 \text{ nA; } V_{DS} = 1 \text{ Drain-source volta}$ $I_D = 12 \text{ mA; } V_{GS} = 1 \text{ Drain-source volta}$ $I_D = 6 \text{ mA; } V_{GS} = 1 \text{ Drain-source volta}$ $I_D = 3 \text{ mA; } V_{GS} = 1 \text{ Drain-source volta}$	cdown voltage = 0 ff voltage = 20 V age (on) $s = 0$ = 0 = 0	$-V_{(BR)GSS}$ $-V_{(P)GS}$ V_{DSon}	> < < > < < < < < < < < < < < < < < < <	50 150 40 4 10		25 75 40 2 5	5 30 40 0.5 3	mA mA
V_{DS} = 20 V; V_{GS} Gate-source break $-I_G$ = 1 μ A; V_{DS} Gate-source cut-o I_D = 1 nA; V_{DS} = Drain-source voltat I_D = 12 mA; V_{GS} = I_D = 6 mA; V_{GS} = I_D = 3 mA; V_{GS} = Drain-source resist	xdown voltage = 0 ff voltage = 20 V age (on) a = 0 = 0 = 0 stance (on)	$\begin{array}{c} -V_{(BR)GSS} \\ -V_{(P)GS} \end{array}$ $\begin{array}{c} V_{DSon} \\ V_{DSon} \end{array}$	> < > < < < < < < < < < < < < < < < < <	50 150 40 4 10 0.4		25 75 40 2 5	5 30 40 0.5 3	mA mA V V V
$V_{DS} = 20 \text{ V; } V_{GS}$ Gate-source break $-I_G = 1 \mu\text{A; } V_{DS}$ Gate-source cut-o $I_D = 1 \text{ nA; } V_{DS} = 1 \text{ Drain-source volta}$ $I_D = 12 \text{ mA; } V_{GS} = 1 \text{ Drain-source resis}$ $I_D = 3 \text{ mA; } V_{GS} = 1 \text{ Drain-source resis}$ $I_D = 0; V_{GS} = 0;$	cdown voltage = 0 ff voltage = 20 V age (on) s = 0 = 0 = 0 etance (on) f = 1 kHz; T _{amb} = 25 °C	$\begin{array}{c} -V_{(BR)GSS} \\ -V_{(P)GS} \end{array}$ $\begin{array}{c} V_{DSon} \\ V_{DSon} \end{array}$	> < > < < < < < < < < < < < < < < < < <	50 150 40 4 10		25 75 40 2 5	5 30 40 0.5 3	mA mA V V V
$V_{DS} = 20 \text{ V; } V_{GS}$ Gate-source break $-I_G = 1 \mu\text{A; } V_{DS}$ Gate-source cut-o $I_D = 1 \text{ nA; } V_{DS} = 1 \text{ mA; } V_{DS} = 1 \text{ mA; } V_{GS} = 1 $	kdown voltage = 0 ff voltage = 20 V age (on) a = 0 = 0 = 0 stance (on) f = 1 kHz; T _{amb} = 25 °C nt	-V _(BR) GSS -V _(P) GS V _{DSon} V _{DSon} V _{DSon}	> < < > < < < < < < < < < < < < < < < <	50 150 40 4 10 0.4 -		25 75 40 2 5	5 30 40 0.5 3	mA mA V V V V
$V_{DS} = 20 \text{ V; } V_{GS}$ $Gate\text{-source break}$ $-I_G = 1 \mu\text{A; } V_{DS}$ $Gate\text{-source cut-o}$ $I_D = 1 \text{ nA; } V_{DS} = 0$ $Drain\text{-source volta}$ $I_D = 12 \text{ mA; } V_{GS} = 0$ $I_D = 6 \text{ mA; } V_{GS} = 0$ $I_D = 3 \text{ mA; } V_{GS} = 0$ $Drain\text{-source resis}$ $I_D = 0; V_{GS} = 0;$ $Drain \text{ cut-off curre}$ $-V_{GS} = 12 \text{ V}$	cdown voltage = 0 ff voltage = 20 V age (on) s = 0 = 0 = 0 etance (on) f = 1 kHz; T _{amb} = 25 °C	-V _{(BR)GSS} -V _{(P)GS} V _{DSon} V _{DSon} V _{DSon} r _{ds on}	> < < > < < < < < < < < < < < < < < < <	50 150 40 4 10 0.4		25 75 40 2 5 - 0.4 -	5 30 40 0.5 3 - - 0.4 100	mA mA V V V V V
$V_{DS} = 20 \text{ V; } V_{GS}$ Gate-source break $-I_G = 1 \mu\text{A; } V_{DS}$ Gate-source cut-o $I_D = 1 \text{ nA; } V_{DS} = 1 \text{ mA; } V_{GS} = 1 $	kdown voltage = 0 ff voltage = 20 V age (on) a = 0 = 0 = 0 stance (on) f = 1 kHz; T _{amb} = 25 °C nt	-V _(BR) GSS -V _(P) GS V _{DSon} V _{DSon} V _{DSon} r _{ds on} I _{DSX}	> <	50 150 40 4 10 0.4 -		25 75 40 2 5	5 30 40 0.5 3	mA mA V V V V V V
$V_{DS} = 20 \text{ V; } V_{GS}$ $Gate\text{-source break}$ $-I_G = 1 \mu\text{A; } V_{DS}$ $Gate\text{-source cut-o}$ $I_D = 1 \text{ nA; } V_{DS} = 1 \text{ Drain-source volta}$ $I_D = 12 \text{ mA; } V_{GS} = 1 \text{ Ind } V_{GS} $	kdown voltage = 0 ff voltage = 20 V age (on) S = 0 = 0 = 0 stance (on) f = 1 kHz; T _{amb} = 25 °C nt V _{DS} = 20 V	-V _(BR) GSS -V _(P) GS V _{DSon} V _{DSon} V _{DSon} r _{ds on} I _{DSX} I _{DSX}	> < < < < < < < < < < < < < < < < < < <	50 150 40 4 10 0.4 - 30 0.1 -		25 75 40 2 5 - 0.4 -	5 30 40 0.5 3 - - 0.4 100	mA mA V V V V V V O nA nA
$V_{DS} = 20 \text{ V; } V_{GS}$ $Gate\text{-source break}$ $-I_G = 1 \mu\text{A; } V_{DS}$ $Gate\text{-source cut-o}$ $I_D = 1 \text{ nA; } V_{DS} = 1000 \text{ ma; } V_{GS} = 10000 \text{ ma; } V_{GS} = 1000 \text{ ma; } V_{GS} = 1000 \text{ ma; } V_{GS} = 10000 \text{ ma; } V_{GS} = 1$	kdown voltage = 0 ff voltage = 20 V age (on) a = 0 = 0 = 0 stance (on) f = 1 kHz; T _{amb} = 25 °C nt	-V _{(BR)GSS} -V _{(P)GS} V _{DSon} V _{DSon} V _{DSon} I _{DSX} I _{DSX} I _{DSX} I _{DSX}	>	50 150 40 4 10 0.4 - 30 0.1 -		25 75 40 2 5 - 0.4 - - - 0.1	5 30 40 0.5 3	mA mA V V V V V V V A nA nA nA μA
$V_{DS} = 20 \text{ V; } V_{GS}$ $Gate\text{-source break}$ $-I_G = 1 \mu\text{A; } V_{DS}$ $Gate\text{-source cut-o}$ $I_D = 1 \text{ nA; } V_{DS} = 1 \text{ Drain-source volta}$ $I_D = 12 \text{ mA; } V_{GS} = 1 \text{ Ind } V_{GS} $	kdown voltage = 0 ff voltage = 20 V age (on) S = 0 = 0 = 0 stance (on) f = 1 kHz; T _{amb} = 25 °C nt V _{DS} = 20 V	-V _(BR) GSS -V _(P) GS V _{DSon} V _{DSon} V _{DSon} r _{ds on} I _{DSX} I _{DSX}	>	50 150 40 4 10 0.4 - 30 0.1 -		25 75 40 2 5 - 0.4 -	5 30 40 0.5 3 - - 0.4 100 - - 0.1	mA mA V V V V V V O nA nA

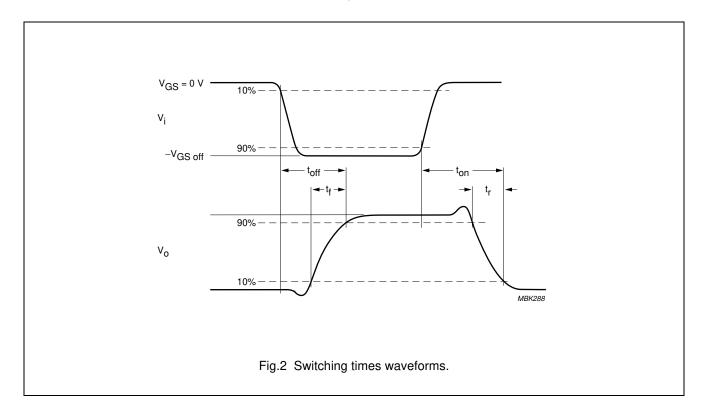
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y-parameters (common source)						
$V_{DS} = 20 \text{ V}; V_{GS} = 0; f = 1 \text{ MHz}; T_{amb} = 25 \text{ °C}$		PMBF4391		PMBF4392	PMBF4393	
Input capacitance	C_{is}	<	14	14	14	pF
Feedback capacitance						
$-V_{GS} = 12 \text{ V}$; $V_{DS} = 0$	C_{rs}	<	3.5	_	_	pF
$-V_{GS} = 7 V$; $V_{DS} = 0$	C_{rs}	<	_	3.5	_	pF
$-V_{GS} = 5 V$; $V_{DS} = 0$	C_{rs}	<	_	_	3.5	pF
Switching times						
$V_{DD} = 10 \text{ V}$; $V_{DS} = 0$						
Conditions I _D and -V _{GSoff}	I_D	=	12	6	3	mA
	$-V_{GS\ off}$	=	12	7	5	V
	R_L	=	750	1550	3150	Ω
Rise time	t_r	<	5	5	5	ns
Turn on time	t _{on}	<	15	15	15	ns
Fall time	t _f	<	15	20	30	ns
Turn off time	t_{off}	<	20	35	50	ns

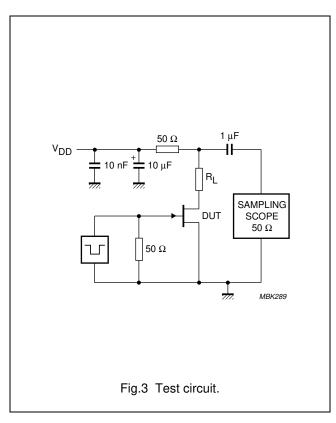
Note

1. Mounted on a ceramic substrate of 8 mm \times 10 mm \times 0,7 mm.



N-channel FETs

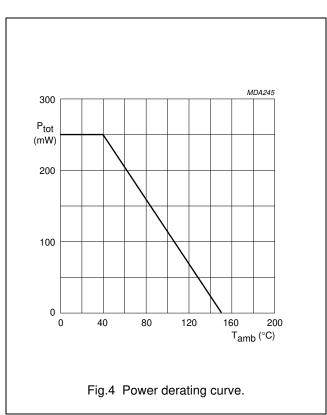
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Pulse generator:

 $\begin{array}{llll} t_r & < & 0.5 & \text{ns} \\ t_f & < & 0.5 & \text{ns} \\ t_p & = & 100 & \mu \text{s} \\ \delta & = & 0.01 & \\ \\ \text{Oscilloscope:} \end{array}$

 $R_i = 50 \Omega$



N-channel FETs

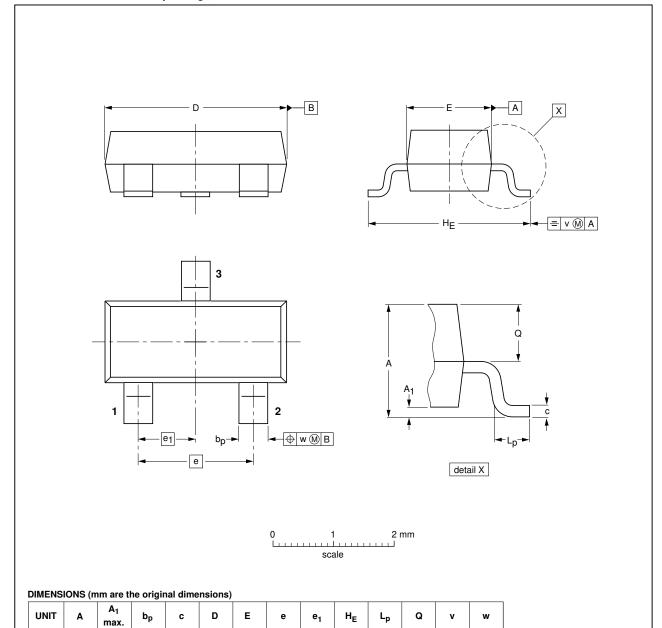
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PMBF4393

PACKAGE OUTLINE

Plastic surface-mounted package; 3 leads

SOT23



OUTLINE	REFERENCES			EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT23		TO-236AB				-04-11-04- 06-03-16

0.95

2.5

2.1

0.45

0.55

0.1

0.2

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0.48

0.38

0.1

0.15

0.09

3.0

1.9

1.1

0.9

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DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

For additional information please visit: http://www.nxp.com

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